TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVII)

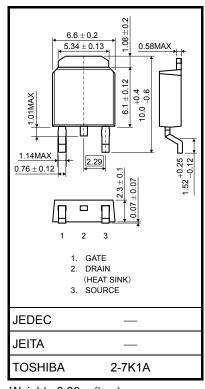
# TK4P60DA

#### Switching Regulator Applications

- Low drain-source ON-resistance: RDS (ON) = 1.7  $\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 2.2 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A (max) (V_{DS} = 600 V)$
- Enhancement-mode:  $V_{th} = 2.4$  to 4.4 V ( $V_{DS} = 10$  V,  $I_D = 1$  mA)

#### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	600	V	
Gate-source voltage		V <sub>GSS</sub>	±30	V	
Drain current	DC (Note 1)	۱ <sub>D</sub>	3.5		
	Pulse (t = 1 ms) (Note 1)	I <sub>DP</sub>	14	A	
Drain power dissipati	on (Tc = 25°C)	PD	80	W	
Single pulse avalanche energy (Note 2)		E <sub>AS</sub>	132	mJ	
Avalanche current		I <sub>AR</sub>	3.5	А	
Repetitive avalanche energy (Note 3)		E <sub>AR</sub>	8	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



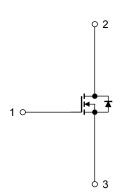
Weight : 0.36 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	1.56	°C/W	
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	125	°C/W	

Internal Connection



Note 1: Please use devices on conditions that the channel temperature is below  $150^{\circ}$ C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 18.9 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 3.5 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm

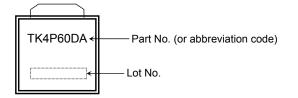
**Electrical Characteristics (Ta = 25°C)** 

Chara	octeristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curr	rent	I <sub>GSS</sub>	$V_{GS}=\pm 30~V,~V_{DS}=0~V$			±1	μA
Drain cut-off curre	ent	I <sub>DSS</sub>	$V_{DS} = 600 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			10	μA
Drain-source brea	akdown voltage	V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	600		_	V
Gate threshold vo	ltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2.4		4.4	V
Drain-source ON-	resistance	R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 1.8 \text{ A}$	_	1.7	2.2	Ω
Forward transfer a	admittance	Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1.8 \text{ A}$	0.6	2.2	_	S
Input capacitance		C <sub>iss</sub>			490	_	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz		3	_	pF
Output capacitance		C <sub>oss</sub>			55	_	
Switching time	Rise time	tr	$V_{GS}$	_	18		
	Turn-on time	t <sub>on</sub>	$\begin{array}{c} & & & \\ & & & & \\ & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & &$		40		• ns
	Fall time	t <sub>f</sub>			8	_	
	Turn-off time	t <sub>off</sub>			55	_	
Total gate charge		Qg			11		
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 3.5 \text{ A}$	_	6		nC
Gate-drain charge		Q <sub>gd</sub>	1	_	5		

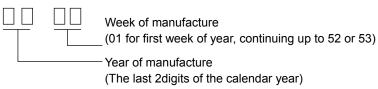
### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	_	_	3.5	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	_		14	А
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 3.5 A, V <sub>GS</sub> = 0 V	_		-1.7	V
Reverse recovery time	t <sub>rr</sub>	$I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V},$	_	1000	_	ns
Reverse recovery charge	Q <sub>rr</sub>	dl <sub>DR</sub> /dt = 100 A/μs	_	5.0	_	μC

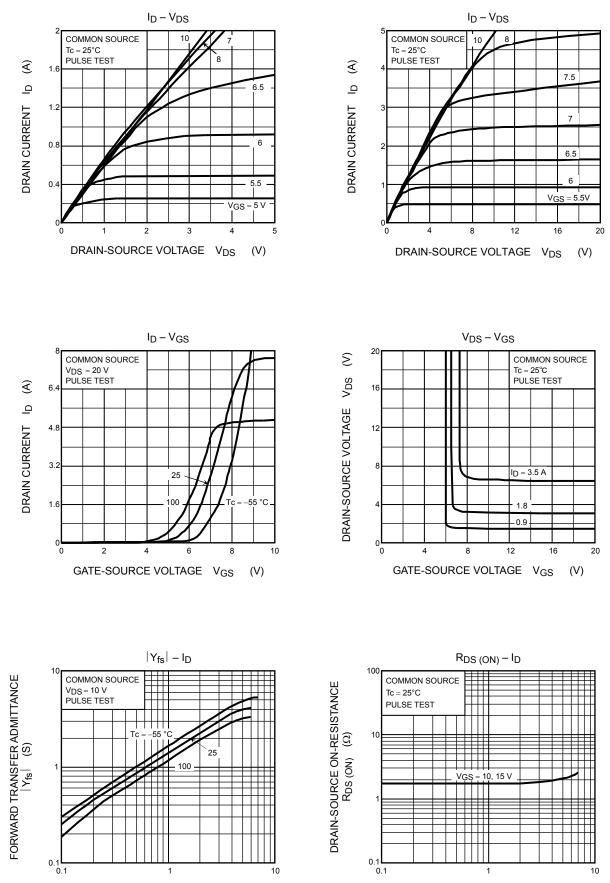
## Marking (Note 4)



Note 4: \* Weekly code: (Four digits)

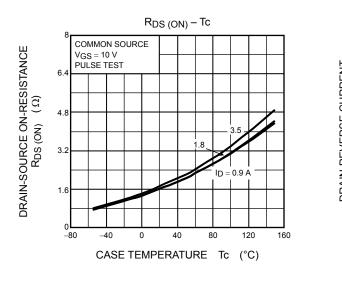


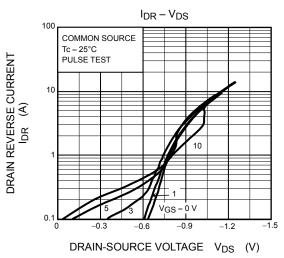
# TOSHIBA

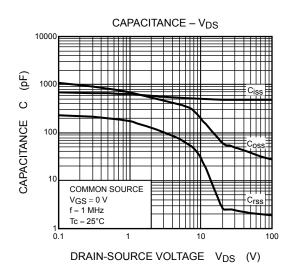


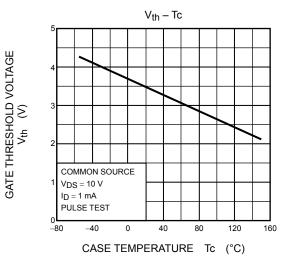
DRAIN CURRENT ID (A)

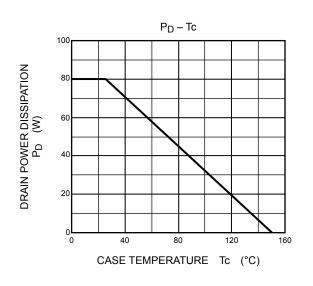
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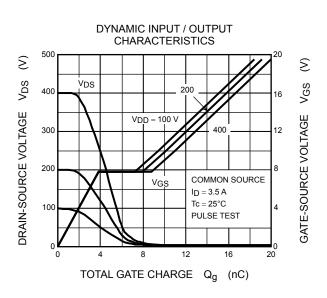


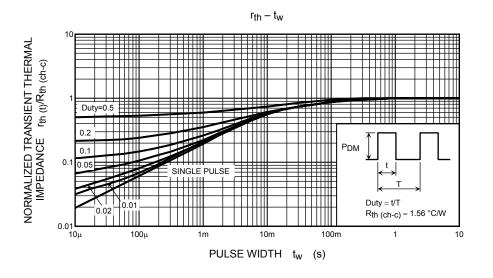


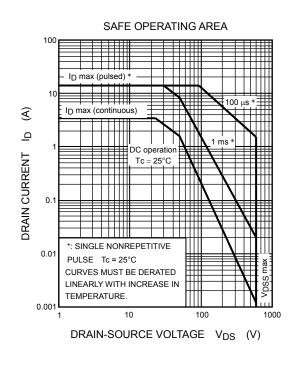


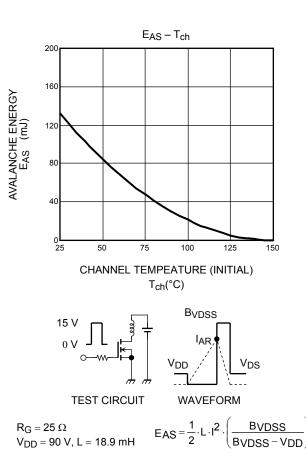












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